

111. (New) A method of producing a semiconductor member comprising a step of forming a semiconductor layer on a substrate by liquid phase epitaxy;

Field
wherein in the liquid phase epitaxy used to form the semiconductor layer, a melting solution in which elements for forming the semiconductor layer are dissolved up to a desired concentration, which is the same as or below saturated concentration, is brought into contact with a surface of the substrate, while a surface temperature of the substrate is made lower than a temperature at which elements in the solution having the desired concentration are saturated by at least 5 degrees Celsius.

REMARKS

Claims 29, 57 to 61, 65 to 67, 88, 94, 95 and 97 to 111 are in the application, with Claims 29, 57 and 111 being the independent claims. Claims 29, 57 to 61, 65 to 67, 88, 94, 95 and 97 to 110 were indicated as being allowed in the Notice Of Allowability mailed February 7, 2003. The claims have not been amended herein, and thus remain in condition for allowance. Claim 111 has been newly-added. Favorable consideration is respectfully requested.

With regard to a formal matter, the Notice Of Allowability mailed February 7, 2003 indicates that new drawings must be submitted to include changes required by the Form PTO-948. However, according to the Form PTO-948 (copy attached), the originally-filed drawings were approved by the Draftsperson. Nevertheless, in the interest of advancing the case to issue, Applicants transmitted another set of formal drawings (identical to the originally-filed drawings) with the Letter Transmitting Formal Drawings

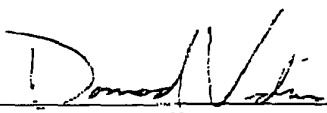
dated February 19, 2003. It is respectfully requested that the next Office communication indicate that the formal drawings have been approved by the Examiner.

It is further requested that the Amendment After Allowance dated February 19, 2003 be entered, and that the next Office communication indicate that the Amendment After Allowance has been so entered.

No other matters being raised, it is believed that the entire application is fully in condition for allowance and such action is courteously solicited.

Applicants' undersigned attorney may be reached in our Costa Mesa, California office at (714) 540-8700. All correspondence should continue to be directed to our below-listed address.

Respectfully submitted,


Attorney for Applicants

Registration No. 52,310

FITZPATRICK, CELLA, HARPER & SCINTO
30 Rockefeller Plaza
New York, New York 10112-2200
Facsimile: (212) 218-2200

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